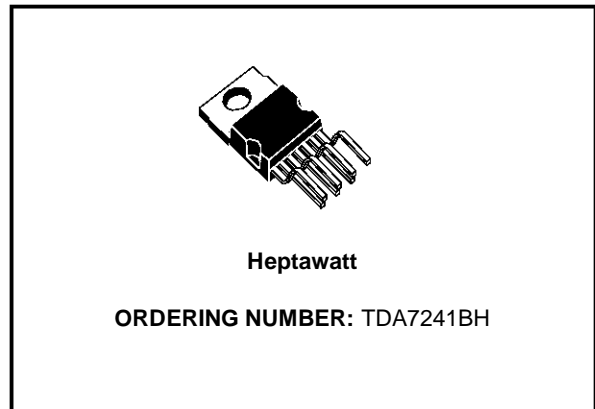


20W BRIDGE AMPLIFIER FOR CAR RADIO

- VERY LOW STAND-BY CURRENT
- GAIN = 32dB
- OUTPUT PROTECTED AGAINST SHORT CIRCUITS TO GROUND AND ACROSS LOAD
- COMPACT HEPTAWATT PACKAGE
- DUMP TRANSIENT
- THERMAL SHUTDOWN
- LOUDSPEAKER PROTECTION
- HIGH CURRENT CAPABILITY
- LOW DISTORTION / LOW NOISE



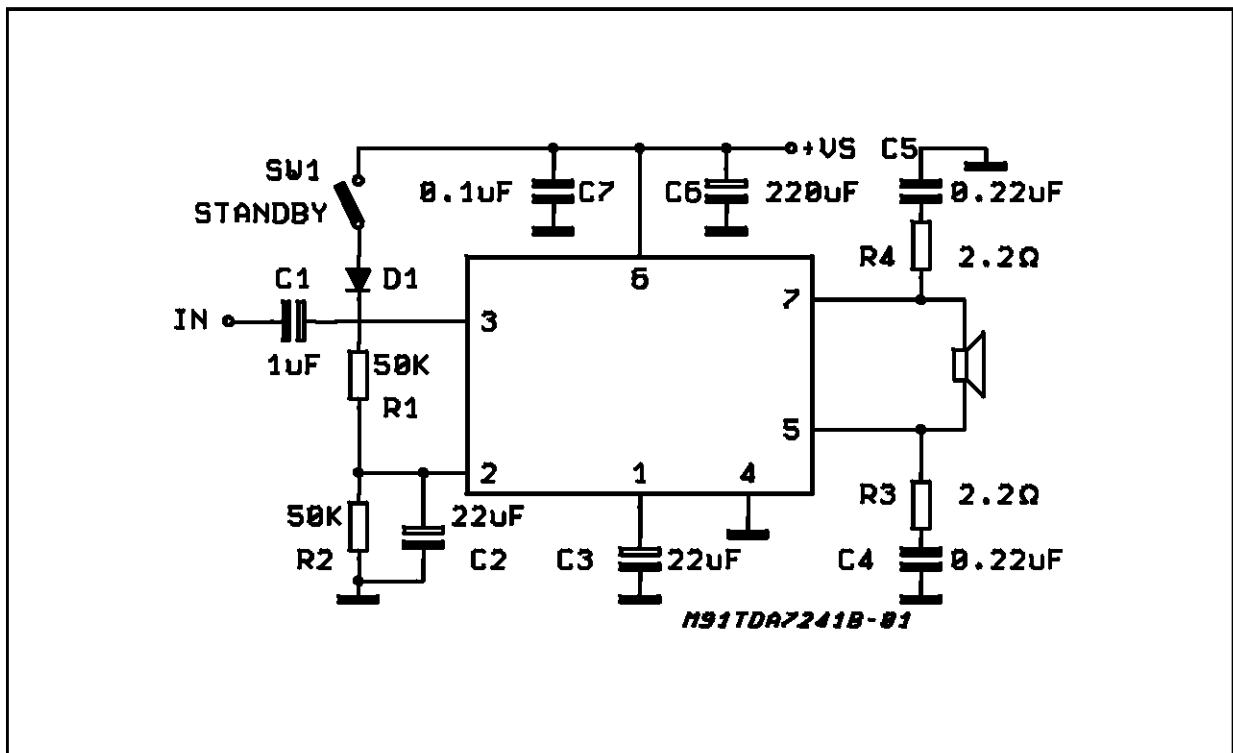
DESCRIPTION

The TDA7241B is a 20W bridge audio amplifier IC designed specially for car radio applications. Thanks to the low external part count and compact Heptawatt 7-pin power package the TDA7241B occupies little space on the printed circuit board.

Reliable operation is guaranteed by a compre-

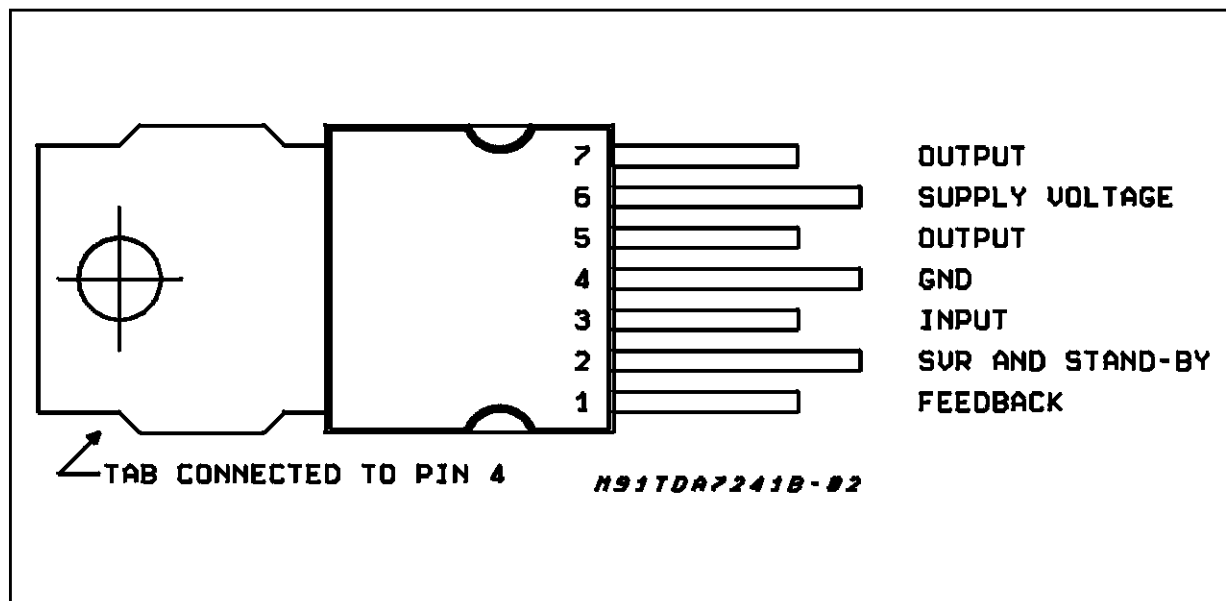
hensive array of on-chip protection features. These include protection against AC and DC output short circuits (to ground and across the load), load dump transients, and junction overtemperature. Additionally, the TDA7241B protects the loudspeaker when one output is short-circuited to ground.

Figure 1: Test and Application Circuit



TDA7241B

PIN CONNECTION (Top view)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_S	Operating Supply Voltage	18	V
V_S	DC Supply Voltage	28	V
V_S	Peak Supply Voltage ($t = 50\text{ms}$)	40	V
I_O	Peak Output Current (non repetitive $t = 0.1\text{ms}$)	4.5	A
I_O	Peak Output Current (repetitive $f \geq 10\text{Hz}$)	3.5	A
P_{tot}	Power Dissipation at $T_{\text{case}} = 85^\circ\text{C}$	16	W
T_{stg}, T_j	Storage and Junction Temperature	-40 to 150	$^\circ\text{C}$

THERMAL DATA

Symbol	Description	Value	Unit
$R_{\text{th j-case}}$	Thermal Resistance Junction-case	Max 4	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS (Refer to the circuit of Fig. 1; $V_S = 14.4V$; R_{th} (heatsink) = $4^{\circ}C/W$, $T_{amb} = 25^{\circ}C$, unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V_S	Supply Range				18	V
I_d	Total Quiescent Current	$R_L = 4\Omega$			80	mA
V_{OS}	Output Offset Voltage				100	mV
P_O	Output Power	$f = 1KHz$ $d = 10\%$ $R_L = 2\Omega$ $R_L = 4\Omega$ $R_L = 8\Omega$	18	26 20 12		W
d	Distortion	$R_L = 4\Omega$ $f = 1KHz$ $P_O = 50mW$ to $12W$		0.1	0.5	%
		$R_L = 8\Omega$ $f = 1KHz$ $P_O = 50mW$ to $6W$		0.05		%
G_V	Voltage Gain	$f = 1KHz$	31	32	33	dB
SVR	Supply Voltage Rejection	$f = 100Hz$ $R_g = 10K\Omega$	40	50		dB
E_n	Total Input Noise	$B = \text{Curve A}$ $R_g = 10K\Omega$		2		μV
		$B = 22Hz$ to $22KHz$ $R_S = 10K\Omega$		3	10	mV
η	Efficiency	$R_L = 4\Omega$ $f = 1KHz$ $P_O = 20W$		65		%
I_{sb}	Stand-by Current				100	μA
R_i	Input Resistance	$f = 1KHz$	70			$K\Omega$
V_i	Input Sensitivity	$f = 1KHz$ $P_O = 2W$ $R_L = 4\Omega$		70		mV
f_L	Low Frequency Roll Off (-3dB)	$P_O = 15W$ $R_L = 4\Omega$		30		Hz
f_H	High Frequency Roll Off (-3dB)	$P_O = 15W$ $R_L = 4\Omega$	25			KHz
A_S	Stand-by Attenuation	$V_O = 2V_{rms}$	70	90		dB
$V_{TH}(pin.2)$	Stand-by Threshold				1	V
T_{sd}	Thermal Shutdown Junction Temp.			150		$^{\circ}C$

(*) B = Curve (***) B = 22Hz to 22KHz

Figure 2: P.C. Board and Component Layout of the Circuit of Fig. 1 (1:1 scale).

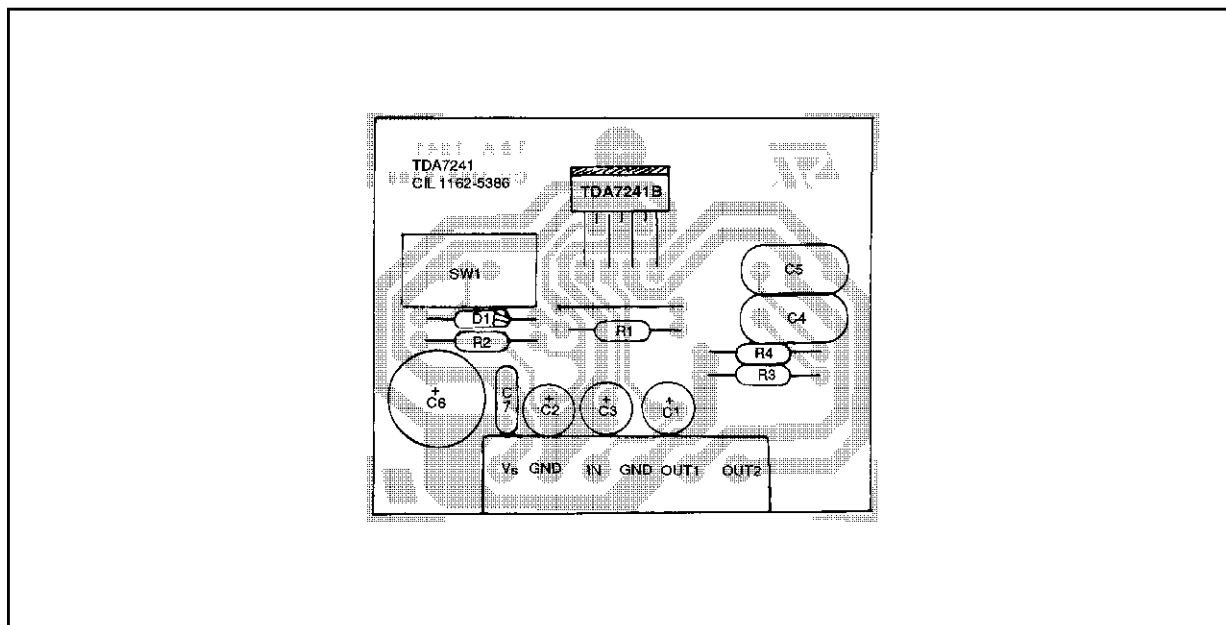


Figure 3: Output Power vs. Supply Voltage

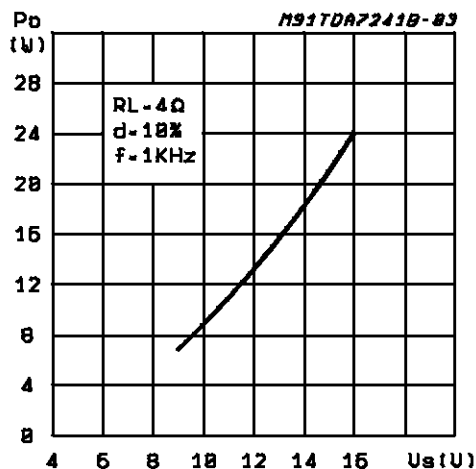


Figure 4: Output Power vs. Supply Voltage

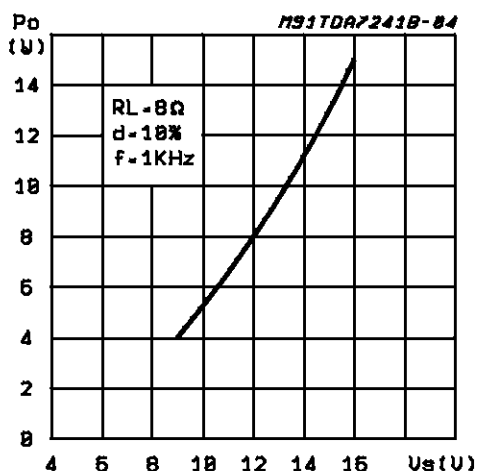


Figure 5: Distortion vs. Output Power

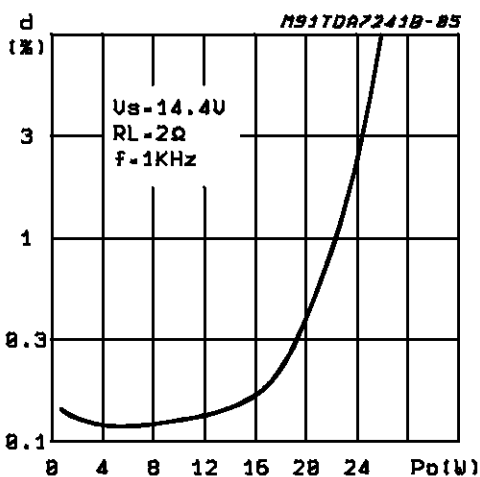


Figure 6: Distortion vs. Output Power

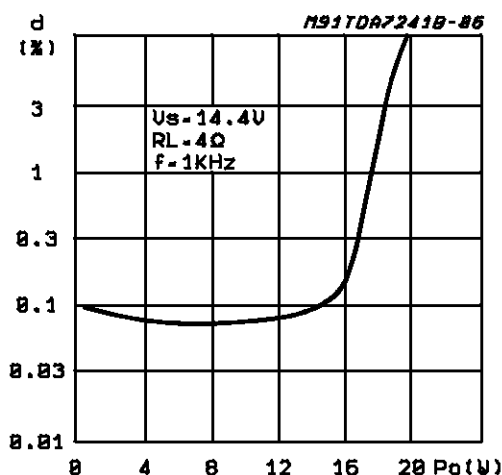


Figure 7: Distortion vs. Output Power

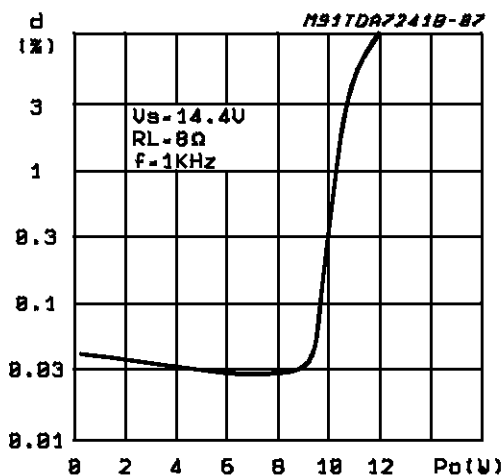


Figure 8: SVR vs. Frequency

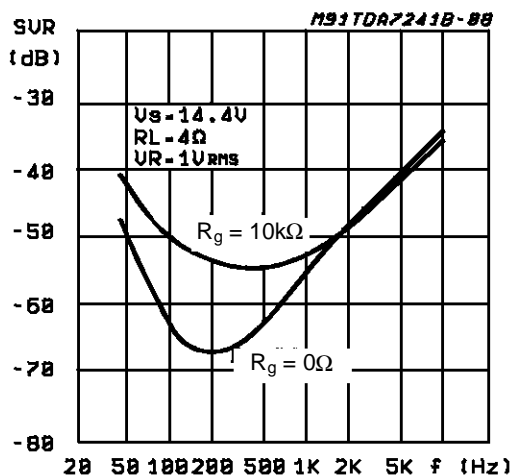


Figure 9: Power Dissipation and Efficiency vs. Output Power

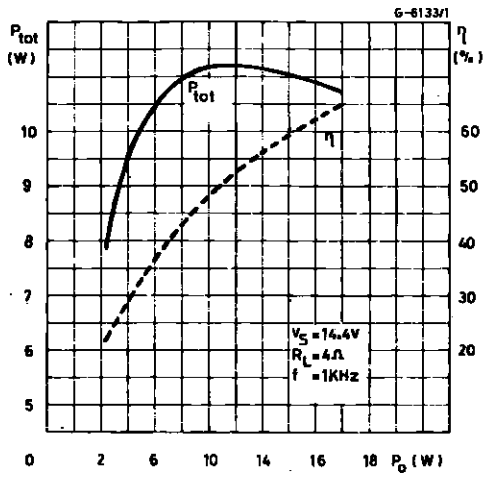
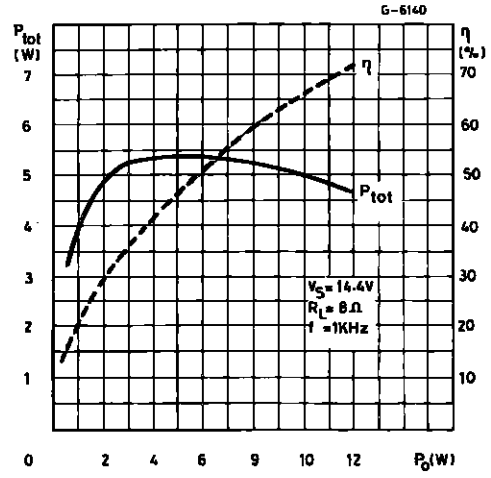
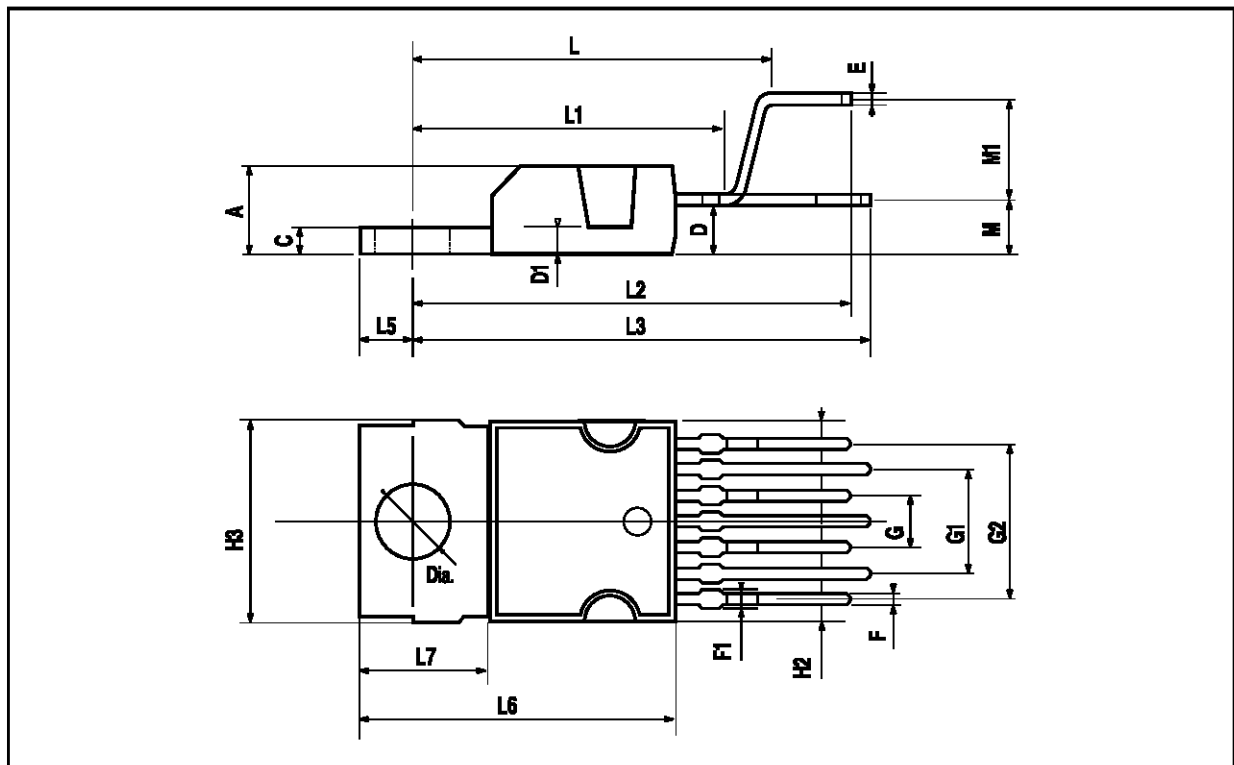


Figure 10: Power Dissipation and Efficiency vs. Output Power



HEPTAWATT PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.6		0.8	0.024		0.031
F1			0.9			0.035
G	2.41	2.54	2.67	0.095	0.100	0.105
G1	4.91	5.08	5.21	0.193	0.200	0.205
G2	7.49	7.62	7.8	0.295	0.300	0.307
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		16.97			0.668	
L1		14.92			0.587	
L2		21.54			0.848	
L3		22.62			0.891	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
M		2.8			0.110	
M1		5.08			0.200	
Dia	3.65		3.85	0.144		0.152



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